

NDF05N50Z, NDP05N50Z, NDD05N50Z

N-Channel Power MOSFET 500 V, 1.25 Ω

Features

- Low ON Resistance
- Low Gate Charge
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	NDF	NDP	NDD	Unit
Drain-to-Source Voltage	V_{DSS}	500			V
Continuous Drain Current $R_{\theta JC}$	I_D	5 (Note 1)	5	4.7	A
Continuous Drain Current $R_{\theta JC}$, $T_A = 100^\circ\text{C}$	I_D	3.2 (Note 1)	3.2	3	A
Pulsed Drain Current, $V_{GS} @ 10\text{ V}$	I_{DM}	20 (Note 1)	20	19	A
Power Dissipation $R_{\theta JC}$	P_D	28	96	83	W
Gate-to-Source Voltage	V_{GS}	± 30			V
Single Pulse Avalanche Energy, $I_D = 5.0\text{ A}$	E_{AS}	130			mJ
ESD (HBM) (JESD22-A114)	V_{esd}	3000			V
RMS Isolation Voltage ($t = 0.3\text{ sec.}$, R.H. $\leq 30\%$, $T_A = 25^\circ\text{C}$) (Figure 17)	V_{ISO}	4500			V
Peak Diode Recovery	dv/dt	4.5 (Note 2)			V/ns
Continuous Source Current (Body Diode)	I_S	5			A
Maximum Temperature for Soldering Leads, 0.063" (1.6 mm) from Case for 10 s Package Body for 10 s	T_L T_{PKG}	300 260			$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J , T_{stg}	-55 to 150			$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

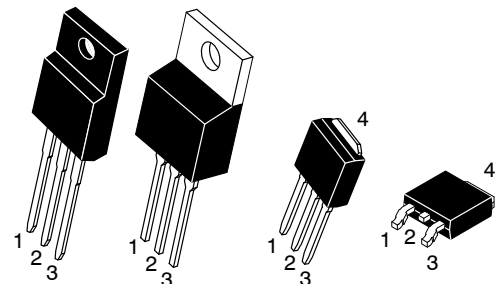
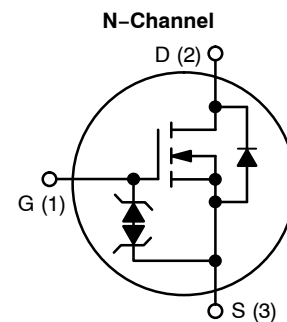
1. Limited by maximum junction temperature
2. $I_S = 4.4\text{ A}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, $T_J = +150^\circ\text{C}$



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V_{DSS}	$R_{DS(on)}$ (TYP) @ 2.2 A
500 V	1.25 Ω



TO-220FP TO-220AB IPAK DPAK
CASE 221D CASE 221A CASE 369D CASE 369AA
STYLE 1 STYLE 5 STYLE 2 STYLE 2

MARKING AND ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

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THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	R _{θJC}	NDP05N50Z	1.3
		NDF05N50Z	4.4
		NDD05N50Z	1.5
Junction-to-Ambient Steady State	R _{θJA}	(Note 3) NDP05N50Z	50
		(Note 3) NDF05N50Z	50
		(Note 4) NDD05N50Z	38
		(Note 3) NDD05N50Z-1	80

3. Insertion mounted

4. Surface mounted on FR4 board using 1" sq. pad size, (Cu area = 1.127 in sq [2 oz] including traces).

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 1 mA	500			V
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D = 1 mA		0.6		V/°C
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	25°C		1	μA
			150°C		50	
Gate-to-Source Forward Leakage	I _{GSS}	V _{GS} = ±20 V			±10	μA

ON CHARACTERISTICS (Note 5)

Static Drain-to-Source On-Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 2.2 A		1.25	1.5	Ω
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 50 μA	3.0		4.5	V
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 2.5 A		3.5		S

DYNAMIC CHARACTERISTICS

Input Capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		530		pF
Output Capacitance	C _{oss}			68		
Reverse Transfer Capacitance	C _{rss}			15		
Total Gate Charge	Q _g	V _{DD} = 250 V, I _D = 5 A, V _{GS} = 10 V		18.5		nC
Gate-to-Source Charge	Q _{gs}			4		
Gate-to-Drain ("Miller") Charge	Q _{gd}			10		
Plateau Voltage	V _{GP}			6.5		
Gate Resistance	R _g			4.5		Ω

RESISTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	t _{d(on)}	V _{DD} = 250 V, I _D = 5 A, V _{GS} = 10 V, R _G = 5 Ω		11		ns
Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(off)}			24		
Fall Time	t _f			14		

SOURCE-DRAIN DIODE CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Diode Forward Voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V			1.6	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, V _{DD} = 30 V		255		ns
Reverse Recovery Charge	Q _{rr}	I _S = 5 A, di/dt = 100 A/μs		1.25		μC

5. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.

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TYPICAL CHARACTERISTICS

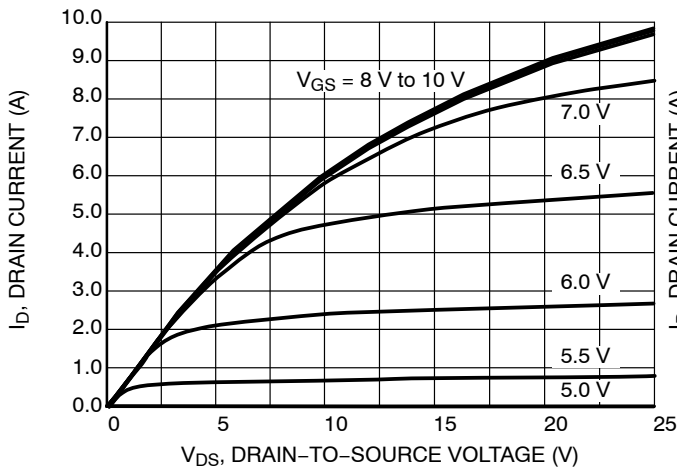


Figure 1. On-Region Characteristics

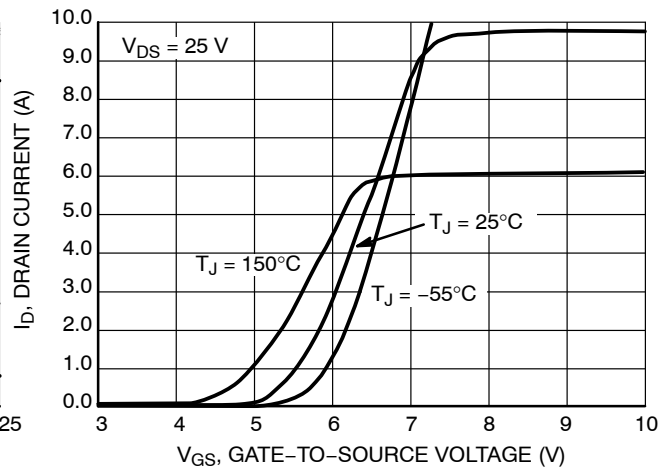


Figure 2. Transfer Characteristics

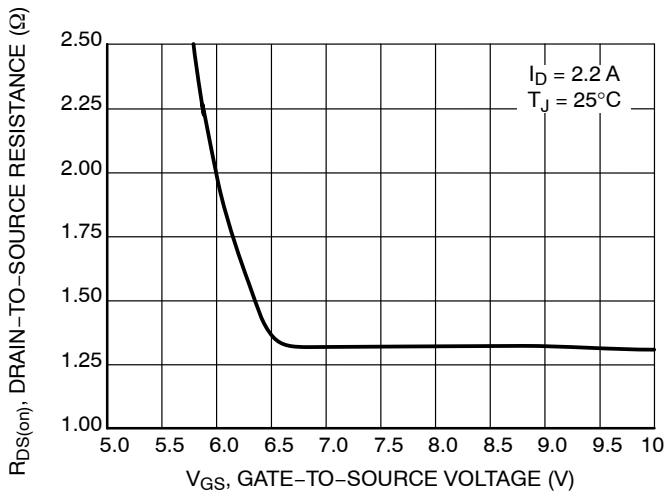


Figure 3. On-Region versus Gate-to-Source Voltage

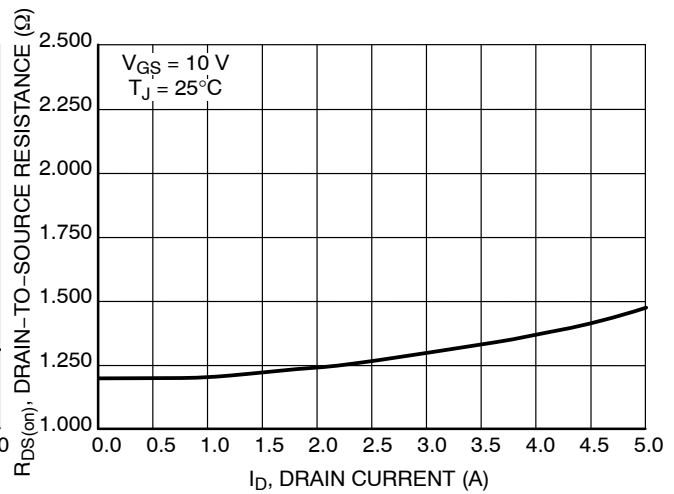


Figure 4. On-Resistance versus Drain Current and Gate Voltage

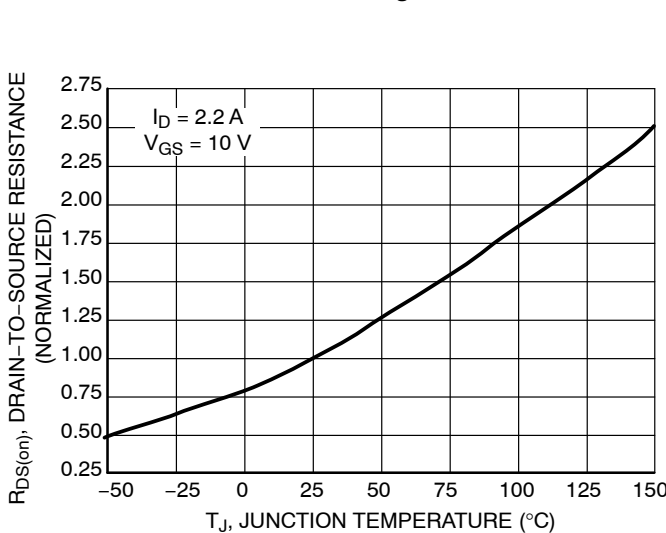


Figure 5. On-Resistance Variation with Temperature

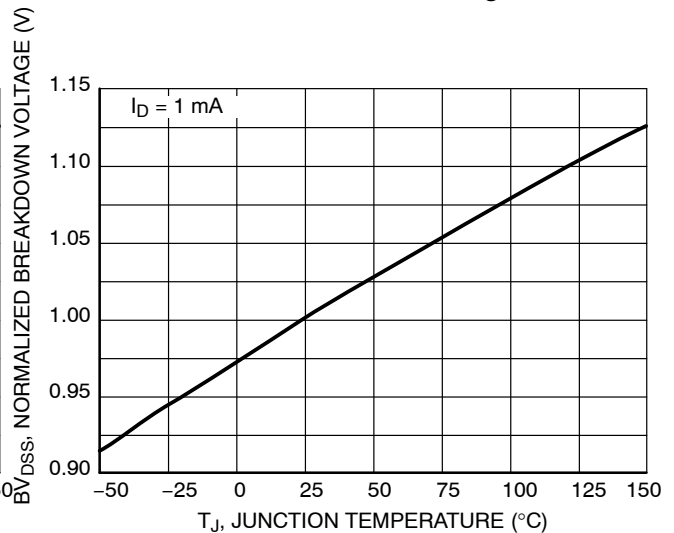


Figure 6. BV_{DSS} Variation with Temperature

TYPICAL CHARACTERISTICS

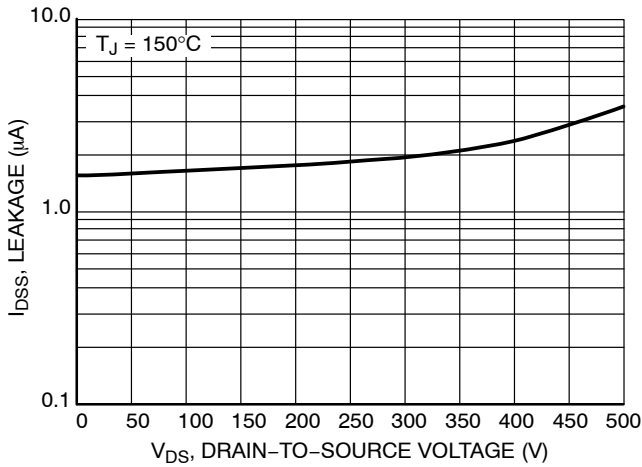


Figure 7. Drain-to-Source Leakage Current versus Voltage

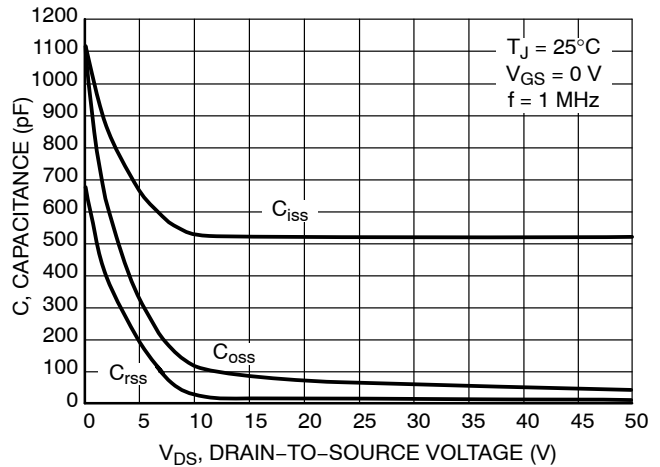


Figure 8. Capacitance Variation

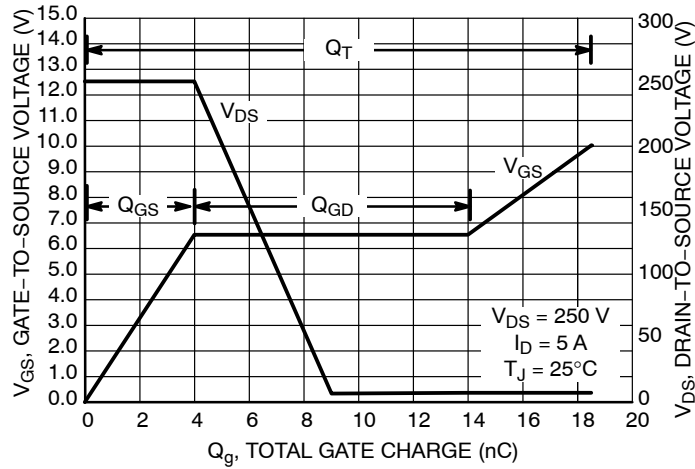


Figure 9. Gate-to-Source Voltage and Drain-to-Source Voltage versus Total Charge

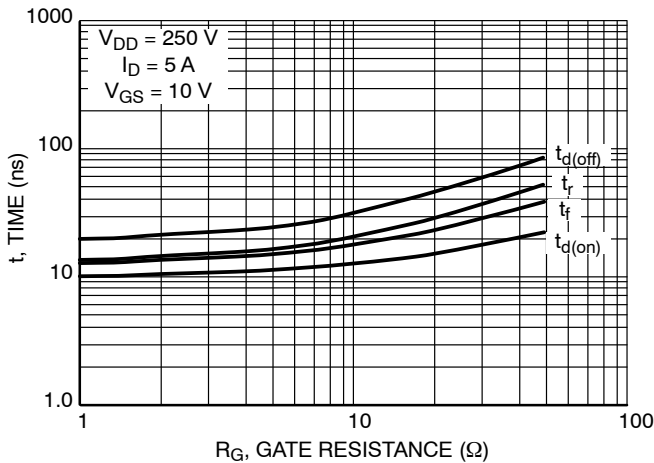


Figure 10. Resistive Switching Time Variation versus Gate Resistance

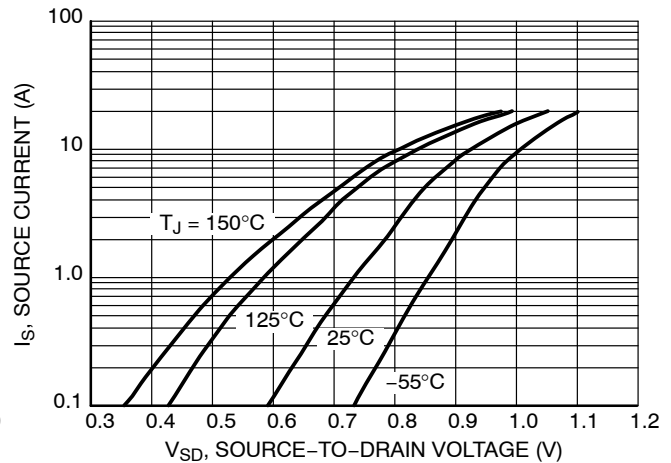


Figure 11. Diode Forward Voltage versus Current

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TYPICAL CHARACTERISTICS

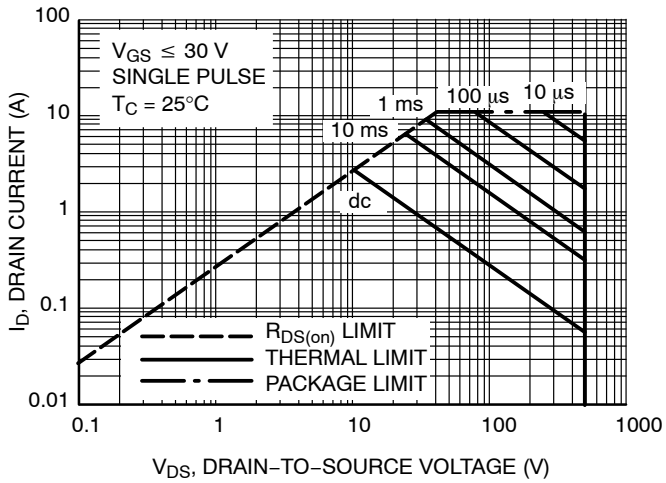


Figure 12. Maximum Rated Forward Biased Safe Operating Area NDF05N50Z

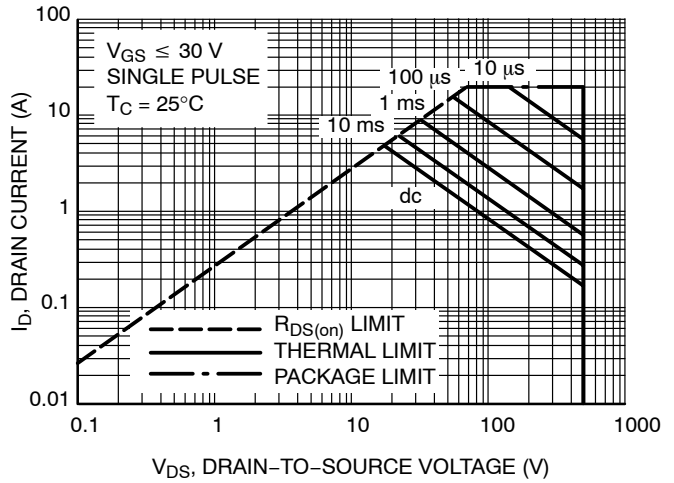


Figure 13. Maximum Rated Forward Biased Safe Operating Area NDD05N50Z

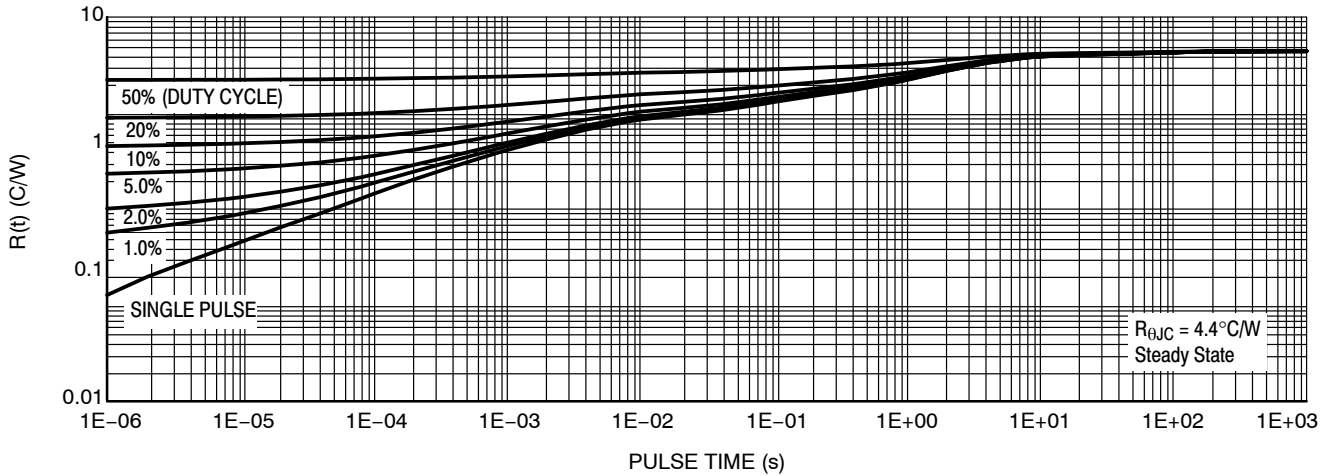


Figure 14. Thermal Impedance (Junction-to-Case) for NDF05N50Z

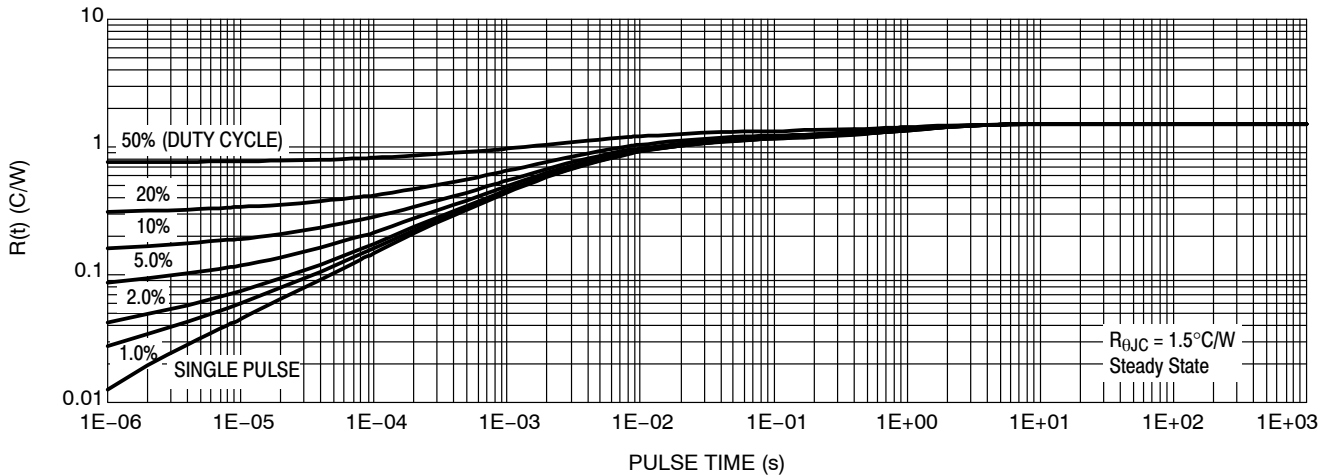


Figure 15. Thermal Impedance (Junction-to-Case) for NDD05N50Z

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TYPICAL CHARACTERISTICS

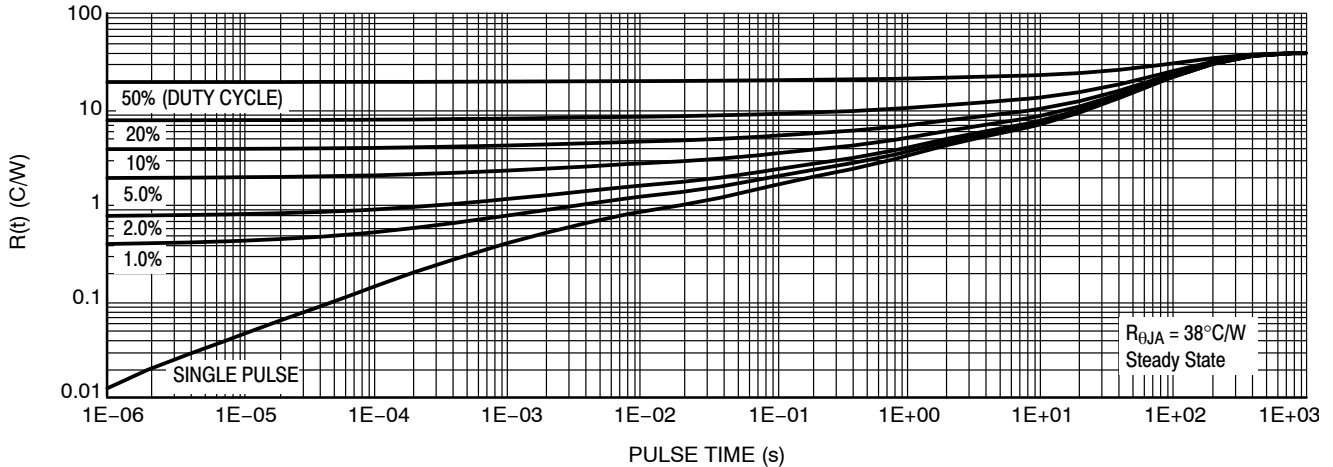


Figure 16. Thermal Impedance (Junction-to-Ambient) for NDD05N50Z

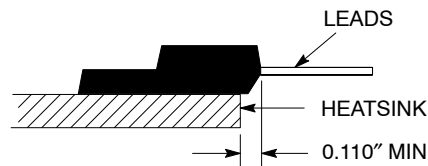


Figure 17. Isolation Test Diagram

Measurement made between leads and heatsink with all leads shorted together.

MOUNTING INFORMATION

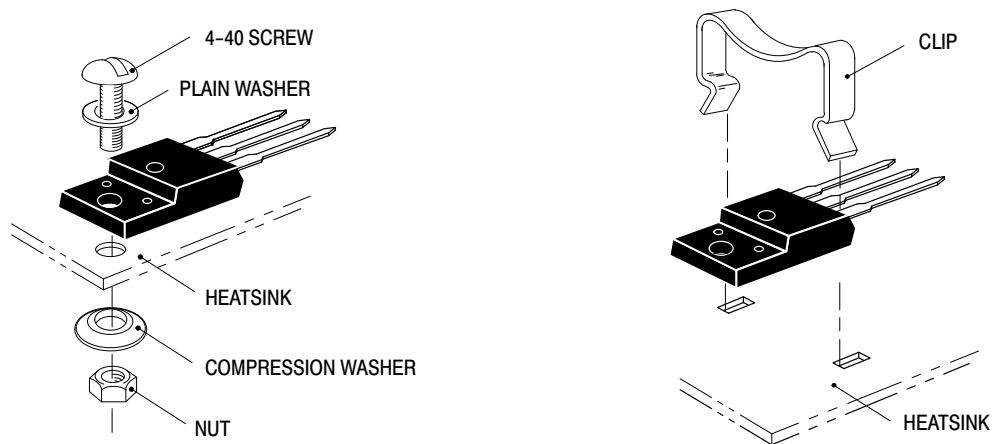


Figure 18. Typical Mounting Techniques*

Laboratory tests on a limited number of samples indicate, when using the screw and compression washer mounting technique, a screw torque of 6 to 8 in · lbs is sufficient to provide maximum power dissipation capability. The compression washer helps to maintain a constant pressure on the package over time and during large temperature excursions.

Destructive laboratory tests show that using a hex head 4-40 screw, without washers, and applying a torque in excess of 20 in · lbs will cause the plastic to crack around the mounting hole, resulting in a loss of isolation capability.

Additional tests on slotted 4-40 screws indicate that the screw slot fails between 15 to 20 in · lbs without adversely affecting the package. However, in order to positively ensure the package integrity of the fully isolated device, ON Semiconductor does not recommend exceeding 10 in · lbs of mounting torque under any mounting conditions.

** For more information about mounting power semiconductors see Application Note AN1040.

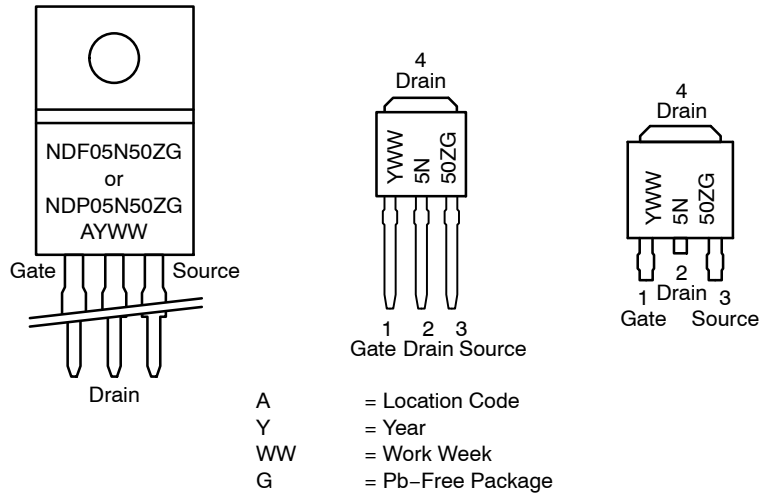
NDF05N50Z, NDP05N50Z, NDD05N50Z

ORDERING INFORMATION

Order Number	Package	Shipping†
NDF05N50ZG	TO-220FP (Pb-Free)	50 Units / Rail
NDP05N50ZG	TO-220AB (Pb-Free)	50 Units / Rail (In Development)
NDD05N50Z-1G	IPAK (Pb-Free)	75 Units / Rail
NDD05N50ZT4G	DPAK (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

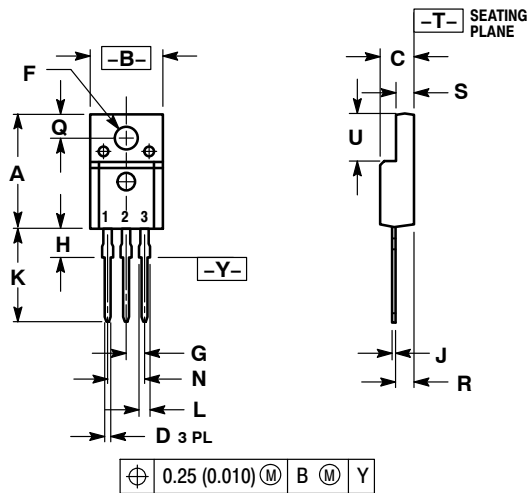
MARKING DIAGRAMS



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PACKAGE DIMENSIONS

TO-220 FULLPAK CASE 221D-03 ISSUE K

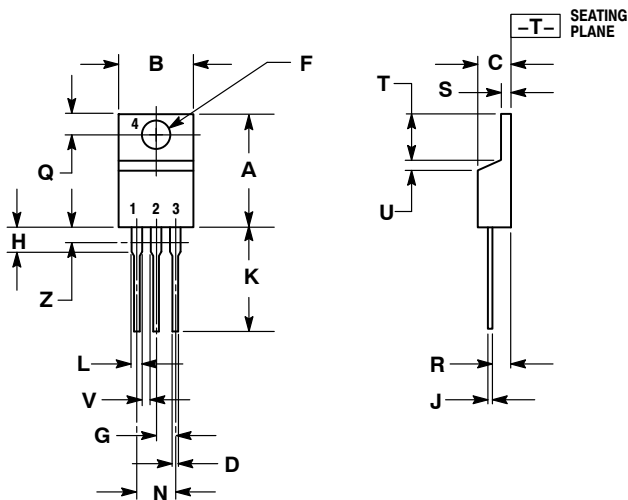


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

- STYLE 1:
1. GATE
 2. DRAIN
 3. SOURCE

TO-220 CASE 221A-09 ISSUE AF



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

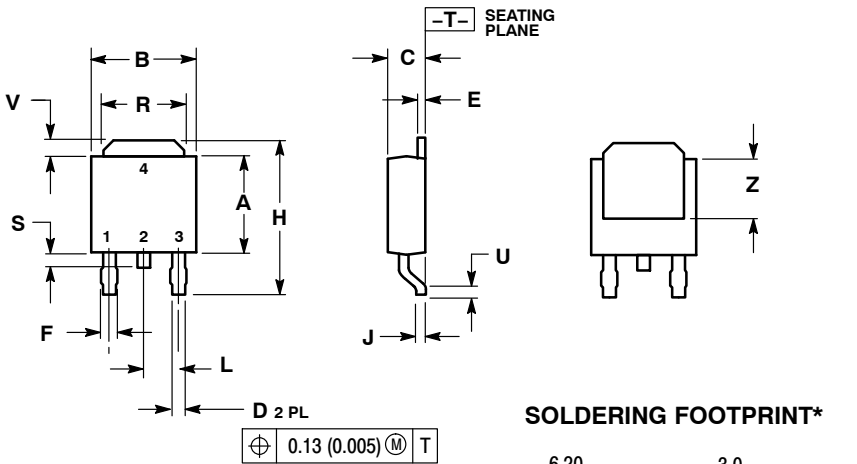
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 5:
1. GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN

NDF05N50Z, NDP05N50Z, NDD05N50Z

PACKAGE DIMENSIONS

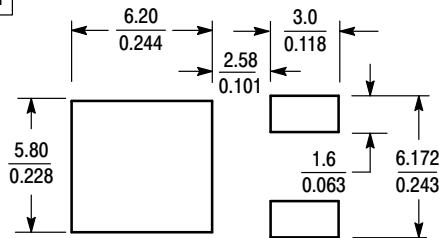
DPAK CASE 369AA-01 ISSUE A



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

SOLDERING FOOTPRINT*

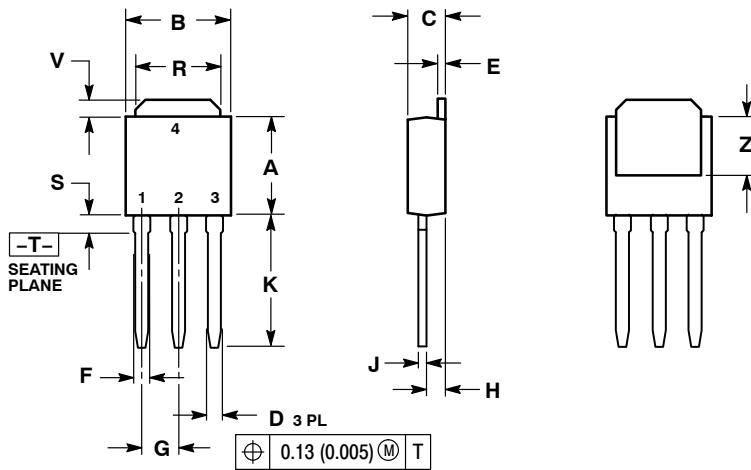


- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

IPAK CASE 369D-01 ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NDF05N50Z, NDP05N50Z, NDD05N50Z

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